Silicon N-Channel MOS FET

HITACHI

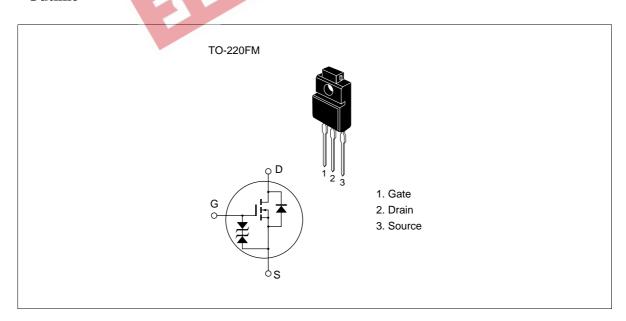
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Tom.cn Suitable for switching regulator and DC-DC converter

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item		Symbol	Ratings	Unit	
Drain to source voltage	2SK1626	V _{DSS}	450	V	
	2SK1627		500		
Gate to source voltage		$V_{\sf GSS}$	±30	V	
Drain current		I _D	5	Α	
Drain peak current	I _{D(pulse)} *1	20	Α		
Body to drain diode reverse	I _{DR}	5	Α		
Channel dissipation	Pch*2	35	W		
Channel temperature		Tch	150	°C	
Storage temperature		Tstg	-55 to +150	°C	
		N.S.	-33 to +130		

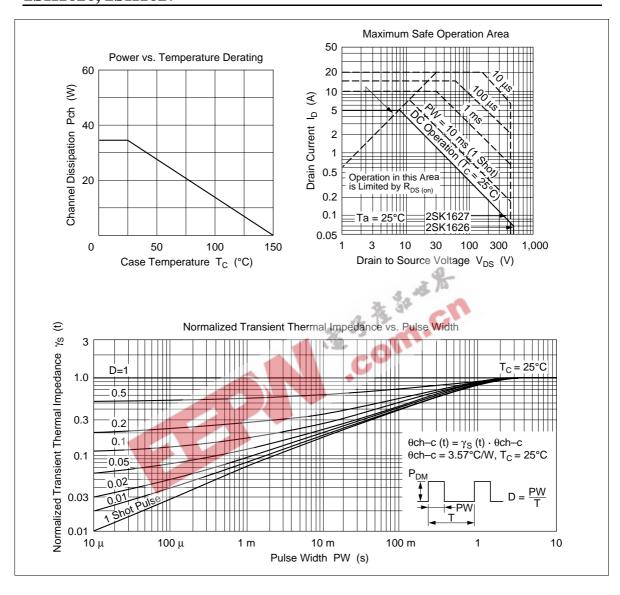


Electrical Characteristics (Ta = 25°C)

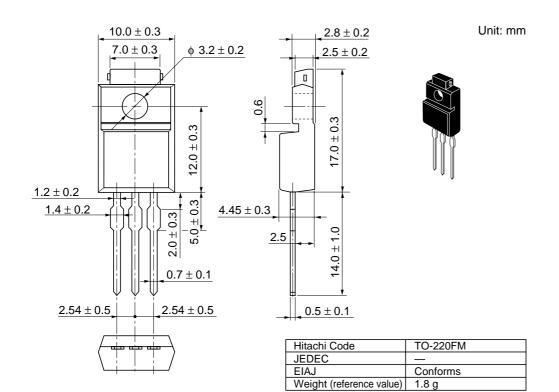
Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source	2SK1626	$V_{(BR)DSS}$	450	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
breakdown voltage	2SK1627	-	500	-			
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak c	urrent	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage	2SK1626	I _{DSS}	_	_	250	μΑ	$V_{DS} = 360 \text{ V}, V_{GS} = 0$
drain current	2SK1627						$V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	_	3.0	V	$I_{D} = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static Drain to source	2SK1626	R _{DS(on)}	_	1.0	1.4	Ω	$I_D = 2.5 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
on state resistance	2SK1627	-	_	1.2	1.5	· 49	
Forward transfer adm	ittance	yfs	2.5	4.0	— ¾	S	$I_D = 2.5 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance		Ciss	_	640	为下	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance		Coss	1	160	_0	pF	f = 1 MHz
Reverse transfer capa	acitance	Crss		20	5	pF	
Turn-on delay time		t _{d(on)}	1/	10	_	ns	$I_D = 2.5 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time		t _r	40	25	_	ns	$R_L = 12 \Omega$
Turn-off delay time		t _{d(off)}	_	50	_	ns	
Fall time		t _f	_	30	_	ns	
Body to drain diode for voltage	orward	V _{DF}	_	0.95	_	V	$I_F = 5 \text{ A}, V_{GS} = 0$
Body to drain diode re recovery time	everse	t _{rr}	_	300	_	ns	$I_F = 5 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Note 1. Pulse test

See characteristic curves of 2SK1155, 2SK1156.







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